





N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	$29m\Omega$ @ $V_{GS} = 4.5V$	5.9A
20V	50mΩ @ V _{GS} = 2.5V	4.3A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use.

Features and Benefits

- Low On-Resistance
- 29mΩ @V_{GS} = 4.5V
- $50 \text{m}\Omega @V_{GS} = 2.5 \text{V}$
- $100m\Omega @V_{GS} = 2.0V$
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

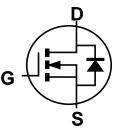
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)

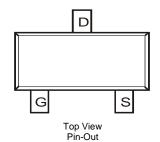
SOT23



Top View



Equivalent Circuit



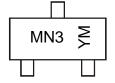
Ordering Information (Note 5)

1			
	Part Number	Case	Packaging
	DMN2050LQ-7	SOT23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



MN3 = Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2008	~		2018	2019	20	20	2021	2022	20	023	2024
Code	V	~		F	G	F	ł	1	J		K	L
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	20	V
Gate-Source Voltage	V _{GSS}	±12	V
Drain Current (Note 6)	I _D	5.9	А
Pulsed Drain Current (Note 7)	I _{DM}	21	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_{D}	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	90	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

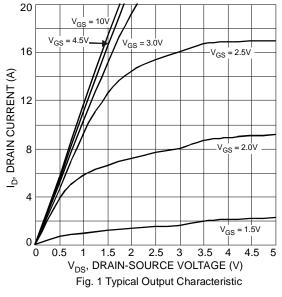
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

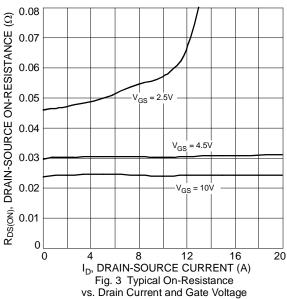
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note7)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	V _{DS} = 20V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)				u .	I.		
Gate Threshold Voltage	V _{GS(TH)}	0.45	_	1.4	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			24	29		V _{GS} = 4.5V, I _D = 5.0A	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	42	50	mΩ	V _{GS} = 2.5V, I _D = 3.1A	
			68	100		V _{GS} = 2.0V, I _D = 1.5A	
Forward Transfer Admittance	Y _{fs}	-	8	_	s	V _{DS} = 5V, I _D = 2.1A	
Diode Forward Voltage (Note 8)	V_{SD}	-	0.9	1.4	V	V _{GS} = 0V, I _S = 2.0A	
DYNAMIC CHARACTERISTICS (Note 9)			•		•		
Input Capacitance	C _{iss}	_	532	_	pF		
Output Capacitance	Coss		144	_	pF	$V_{DS} = 10V, V_{GS} = 0V$ $f = 1.0MHz$	
Reverse Transfer Capacitance	C _{rss}		117	_	pF	1 - 1.000112	
Gate Resistance	Rg	-	1.3	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
SWITCHING CHARACTERISTICS (Note 9)							
Total Gate Charge	Qg	1	6.7	_		$V_{DS} = 10V, V_{GS} = 4.5V, I_{D} = 5.0A$	
Gate-Source Charge	Q_{gs}		0.8	_	nC	$V_{DS} = 10V, V_{GS} = 4.5V, I_{D} = 5.0A$	
Gate-Drain Charge	Q _{gd}	_	3.0	_		$V_{DS} = 10V, V_{GS} = 4.5V, I_{D} = 5.0A$	

Notes:

- 6. Device mounted on FR-4 PCB, on 2oz Copper pad layout with $R_{\theta JA} = 90^{\circ}$ C/W. 7. Repetitive rating, pulse width limited by junction temperature.
- 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to production testing.







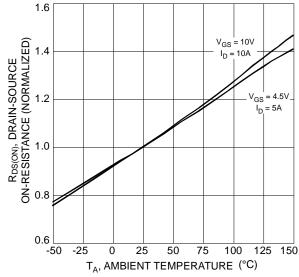
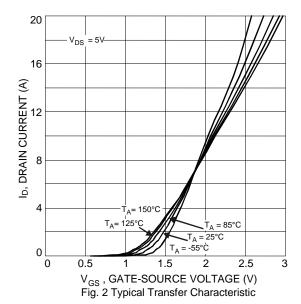
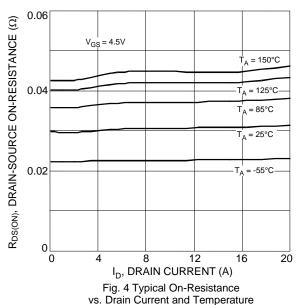


Fig. 5 On-Resistance Variation with Temperature

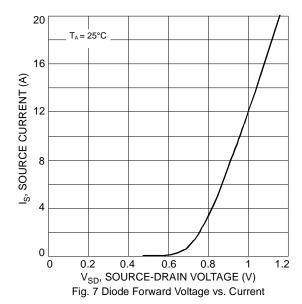


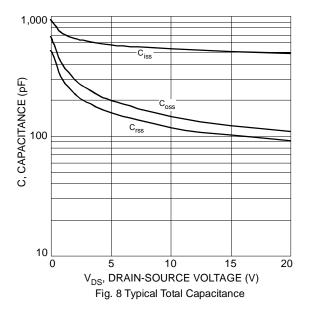


1.6 $V_{\text{GS}(\text{TH})}$, GATE THRESHOLD VOLTAGE (V) 1.2 1.0 I_D = 250μA 8.0 0.6 0.4 0 -50 -25 25 50 75 100 125 T_A, AMBIENT TEMPERATURE (°C)

Fig. 6 Gate Threshold Variation vs. Ambient Temperature







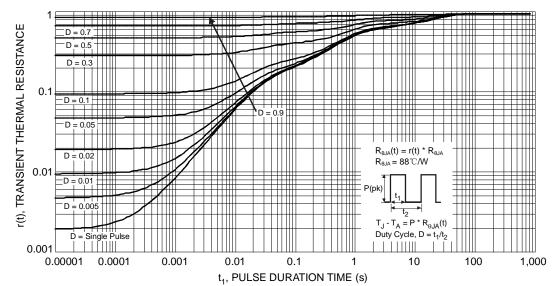
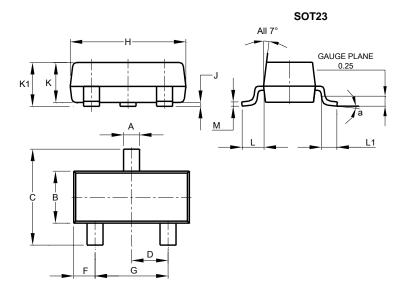


Fig. 9 Transient Thermal Response



Package Outline Dimensions

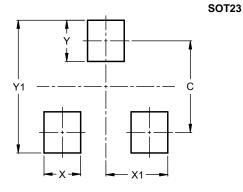
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23							
Dim	Min	Max	Тур				
A	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
V1	2.0



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